

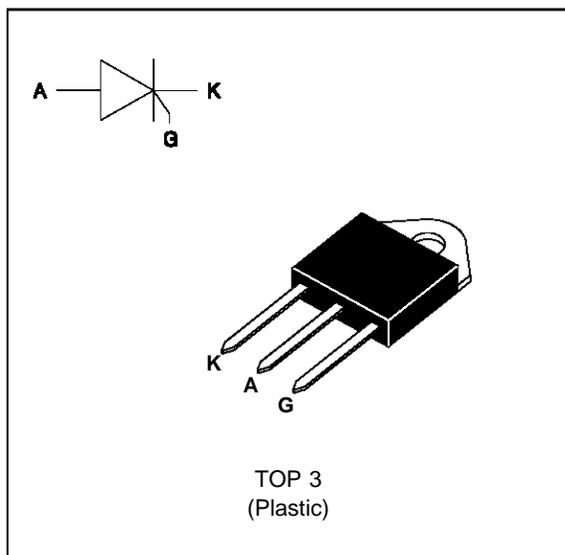
FEATURES

- HIGH SURGE CAPABILITY
- HIGH ON-STATE CURRENT
- HIGH STABILITY AND RELIABILITY
- BTW 69 Serie :
INSULATED VOLTAGE = 2500V_(RMS)
(UL RECOGNIZED : E81734)

DESCRIPTION

The BTW 69 (N) Family of Silicon Controlled Rectifiers uses a high performance glass passivated technology.

This general purpose Family of Silicon Controlled Rectifiers is designed for power supplies up to 400Hz on resistive or inductive load.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit	
I _{T(RMS)}	RMS on-state current (180° conduction angle)	BTW 69	T _c =70°C	50	A
		BTW 69 N	T _c =75°C	55	
I _{T(AV)}	Average on-state current (180° conduction angle, single phase circuit)	BTW 69	T _c =70°C	32	A
		BTW 69 N	T _c =75°C	35	
I _{TSM}	Non repetitive surge peak on-state current (T _j initial = 25°C)		tp=8.3 ms	525	A
			tp=10 ms	500	
I ² t	I ² t value		tp=10 ms	1250	A ² s
di/dt	Critical rate of rise of on-state current Gate supply : I _G = 100 mA di _G /dt = 1 A/μs			100	A/μs
T _{stg} T _j	Storage and operating junction temperature range			- 40 to + 150 - 40 to + 125	°C °C
T _l	Maximum lead temperature for soldering during 10 s at 4.5 mm from case			230	°C

Symbol	Parameter	BTW 69		BTW 69 / BTW 69 N				Unit
		200	400	600	800	1000	1200	
V _{DRM} V _{RRM}	Repetitive peak off-state voltage T _j = 125 °C	200	400	600	800	1000	1200	V